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[0040] Exemplary voltages for the programming, erase and reading operations of the memory are described in the aforementioned U.S. patent no. 6,355,524.

IN THE CLAIMS

1. (Amended) A method for forming cobalt silicide on a body which has a surface that comprises silicon, the method comprising:

forming a cobalt layer on said surface;



forming a titanium layer over the cobalt layer by ionized physical vapor deposition while the body is attached to a support biased with an AC power of 0 W;

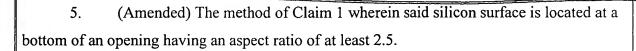
reacting the cobalt with the silicon to form cobalt silicide; and removing the titanium layer, and if any cobalt has not reacted with the silicon then

Please cancel Claim 2.

removing the unreacted cobalt.

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- 3. (Amended) The method of Claim 1 wherein during the titanium layer deposition the distance between a titanium target and the body is at least 140 mm.
- 4. (Unchanged) The method of Claim 1 wherein the titanium layer is at most 7.5 nm thick.





6. (Amended) The method of Claim 5 wherein at least part of a sidewall surface of the opening is made of a dielectric:

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7. (New) The method of Claim 1 wherein the titanium layer is deposited on the cobalt layer to be in contact with the cobalt layer.

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